

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013 PHONE: (215) 631-9840 FAX: (215) 631-9855

MS1576

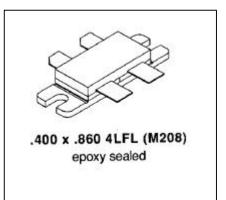
RF & MICROWAVE TRANSISTORS TV LINEAR APPLICATIONS

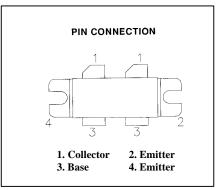
Features

- 470 860 MHz
- 28 VOLTS
- P_{OUT} = 100 W
- $G_P = 8.5 \text{ dB MINIMUM}$
- INPUT/OUTPUT MATCHING
- COMMON EMITTER CONFIGURATION

DESCRIPTION:

The MS1576 is a gold metallized NPN planar transistor designed for high linearity Class AB operation in UHF and Band IV, V television transmitters and transposers. The MS1576 utilizes an emitter ballasted die geometry for superior ruggedness and reliability.





ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	65	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	3.5	V
I _C	Device Current	16	Α
P _{DISS}	Power Dissipation	220	W
TJ	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

R _{TH(J-C)}	Thermal Resistance Junction-case	0.8	°C/W
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MS1576

ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol	Test Conditions		Value	Unit			
Symbol			Mir	. Typ.	Max.	Onic	
BV _{CBO}	I _c = 40 mA	I _E = 0mA	65			V	
BV _{CEO}	I _C = 80mA	I _B = 0mA	30			V	
BV _{CER}	I _c = 120mA	R _{BE} = 75 Ω	40			V	
BVEBO	I _E = 20mA	I _C = 0mA	3.5			V	
I _{CEO}	V _{CE} = 28V	I _в = 0mА			10	mA	
h _{FE}	$V_{CE} = 5V$	$I_{C} = 4A$	25		120		

DYNAMIC

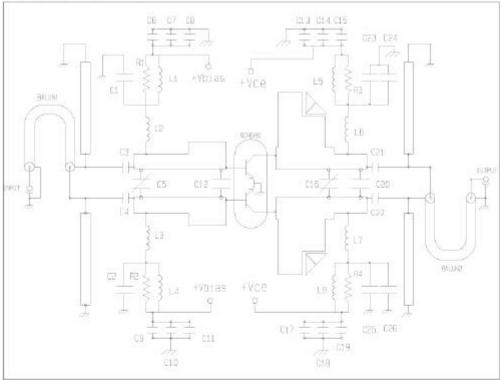
Symbol	Test Conditions			Value			Unit
Symbol	Symbol Test Conditions				Typ.	Max.	Onit
P _{1dB}	f = 860 MHz	P _{REF} = 25 W	I _{CQ} =200mA	100			W
G _p	f = 860 MHz	P _{OUT} = 100 W	I _{CQ} =200mA	8.5			dB
ης	f = 860 MHz	P _{OUT} = 100 W	I _{CQ} =200mA	55			%
Сов	f = 1 MHz	V _{CB} = 28 V			50		pf



MS1576

TEST CIRCUIT

TEST CIRCUIT SCHEMATIC



TEST CIRCUIT COMPONENT PART LIST

PCB	ROGERS, er = 2.55, Height = 31.25 mil 1 oz. Cu.
Balun 1,2	50 W Coaxial Cable Lenght 2.2" attached to 2 x 50 W printed microstrip transmission lines (see photomaster)
C1, C2, C23, C25	75pF Ceramic Chip ATC B
C3, C4, C21, C22	2 x 47pF Ceramic Chip, ATC B
C5, C16	0.8 - 8pF Variable, JOHANSON Giga - Trim
C6, C9	750pF Ceramic Chip, ATC B
C7, C10	39nF Ceramic Chip, ATCB
C8, C11, C24, C26	47mF, 50V Electrolytic
C13, C17	100mF, 50V Electrolytic
C12	9.1pF, Ceramic Chip, ATC A
C14, C18	39nF Ceramic Chip (OPTIONAL)
C15, C19	750pF Ceramic Chip (OPTIONAL)
C20	1.3pF Ceramic Chip, ATC B
L1, L4, L5, L8	12 Turns, #200 AWG, 0.15" I.D. (Tight)
L2, L3, L6, L7	4 Turns, #20AWG, 0.13" I.D. (1:1)
R1, R2, R3, R4	5 X 50 W Chip Resistor

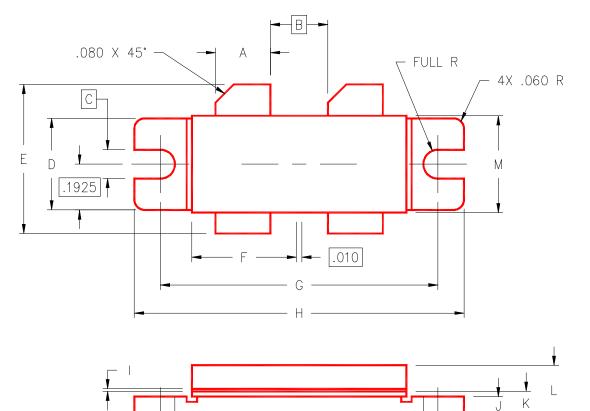
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PACKAGE MECHANICAL DATA

PACKAGE STYLE M208



	MINIMUM	MAXIMUM		MINIMUM	MAXIMUM
	INCHES/MM	INCHES/MM		INCHES/MM	INCHES/MM
Α	.220/5,59	.230/5,84		.003/0,08	.007/0,18
В	.210/	/5,33	J	.060/1,52	.070/1,78
С	.125/3,18		К	.100/2,54	.115/2,92
D	.380/9,65	.390/9,91	L		.230/5,84
E	.580/14,73	.620/15,75	М	.395/10,03	.405/10,29
F	.420/10,67	.430/10,93			
G	1.090/27,69	1.105/28,07			
Н	1.335/33,91	1.345/34,16			

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